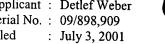
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## In the claims:

Please amend the claims as follows:

## 1-14 (Cancelled)

## 14-20 (Withdrawn)

21. (Currently Amended) A method for fabricating a metallization arrangement for a semiconductor structure, said method comprising:

providing a first [substructure] metallization plane on said semiconductor structure; providing a first intermediate dielectric on said first [substructure] metallization plane; providing a liner layer made of a dielectric material on said first intermediate dielectric [substructure plane];

providing via holes in said first intermediate dielectric and said liner layer, said via holes being filled with a conductive material, thereby completing a first resulting structure;

providing a second metallization plane on said first resulting structure;

patterning a first interconnect in said second metallization plane;

patterning a second interconnect in said second metallization plane;

interrupting said liner layer between said first interconnect and said second interconnect, thereby forming an interspace between said first and second interconnects.

- 22. (Previously Added) The method as claimed in claim 21, wherein patterning and interrupting are carried out in a common etching step.
- 23. (Previously Added) The method as claimed in claim 21, further comprising providing an electrical circuit integrated into a silicon substrate.

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24. (Previously Added) The method as claimed in claim 23, wherein providing a liner layer comprises fabricating said liner layer from a material selected from the group consisting of silicon dioxide and silicon nitride.

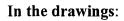
25. (Previously Added) The method as claimed in claim 24, wherein said patterning is carried out in a first metal etching step and said interrupting is carried out in a second silicon dioxide etching step.

- 26. (Previously Added) The method as claimed in claim 21, further comprising providing a dielectric in said interspace.
- 27. (Currently Amended) The method as claimed in claim 21, further comprising providing <u>a</u> mask on said second metallization plane for use in patterning and interrupting.

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Please substitute the enclosed FIG. 2 for the FIG. 2 presently in the application. The enclosed FIG. 2 is labeled as prior art, consistent with the Examiner's suggestion.